



Package: Hermetic, 2-pin, 5.8mm x 2.8mm

Product Description

RFMD's SBB-2082S is a high performance InGaP HBT utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 5V supply, the SBB-2082S does not require a dropping resistor as compared to typical Darlington amplifiers. The SBB-2082S product is designed for high linearity 5V gain block applications that require small size and minimal external components. It is internally matched to 50Ω.

RFMD can provide various levels of device screening for military or Hi-Rel applications.

Features

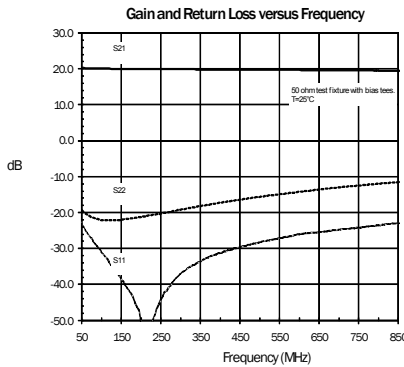
- Hermetic Package for Hi Rel Applications
- Single Fixed 5V Supply
- Patented Thermal Design and Bias Circuit
- OIP3 = 40.5 dBm at 70 MHz
- P1dB = 19.5 dBm at 70 MHz

Applications

- Military Communications
- Aerospace and Defense
- PA Driver Amp

Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- RF MEMS



| Parameter | Specification | | | Unit | Condition |
|------------------------------------|---------------|------|------|------|--------------------------|
| | Min. | Typ. | Max. | | |
| Frequency of Operation | 50 | | 850 | MHz | |
| Supply Voltage | | 5.0 | | V | |
| Supply Current | 75 | 86 | 98 | mA | |
| Small Signal Gain | 18.5 | 20.2 | | dB | Freq = 100MHz |
| | | 19.8 | | dB | Freq = 500MHz |
| Output Power at 1 dB Compression | 18.0 | 19.5 | | dBm | Freq = 70 MHz |
| Output Third Order Intercept Point | 38.5 | 40.5 | | dBm | F1 = 70 MHz, F2 = 71 MHz |
| Input Return Loss | 9.5 | 25 | | dB | Freq = 100MHz |
| | | 25.0 | | dB | Freq = 500MHz |
| Output Return Loss | 9.5 | 20 | | dB | Freq = 100 MHz |
| | | 15.0 | | dB | Freq = 500 MHz |
| Reverse Isolation | 19 | 22 | | dB | Freq = 100 MHz |
| | | 22.0 | | dB | Freq = 500 MHz |
| Noise Figure | | 3.1 | | dB | Freq = 500 MHz |
| Thermal Resistance | | 45 | | °C/W | Junction to lead |

Test Conditions: Z₀ = 50Ω, V_D = 5V, I_D = 86mA, T = 25 °C, OIP3 P_{OUT}/tone = 0 dBm, 50Ω test fixture with bias tees.

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|--------------------------------------|-------------|------|
| Total Current (I_D) | 110 | mA |
| Device Voltage (V_D) | 5.5 | V |
| RF Input Power | +24 | dBm |
| Operating Lead Temperature (T_L) | -40 to +85 | °C |
| Storage Temperature Range | -55 to +150 | °C |
| Operating Junction Temp (T_J) | +150 | °C |
| Moisture Sensitivity Level | Hermetic | |
| ESD Rating - Human Body Model (HBM) | Class 2 | |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

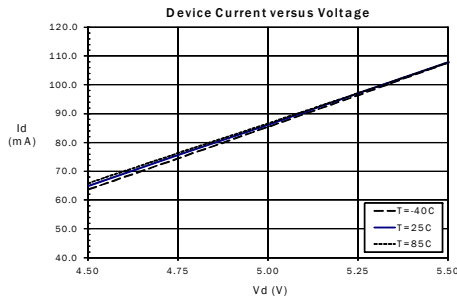
RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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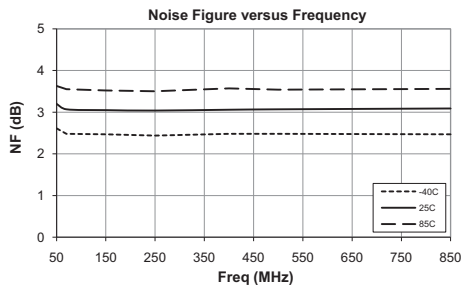
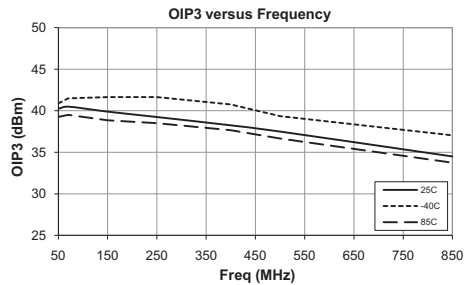
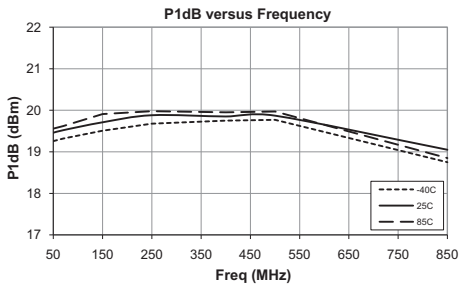
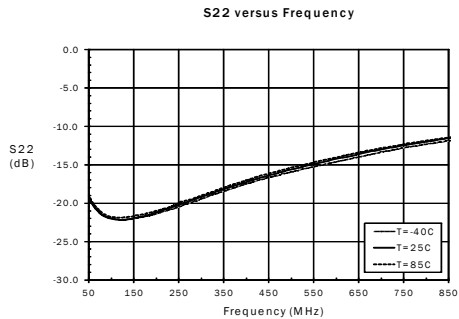
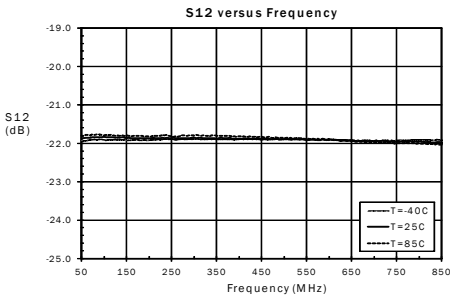
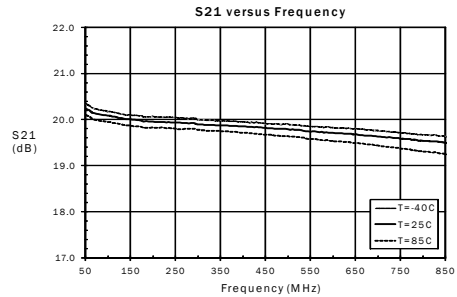
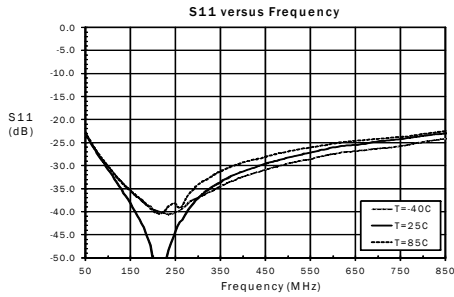
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

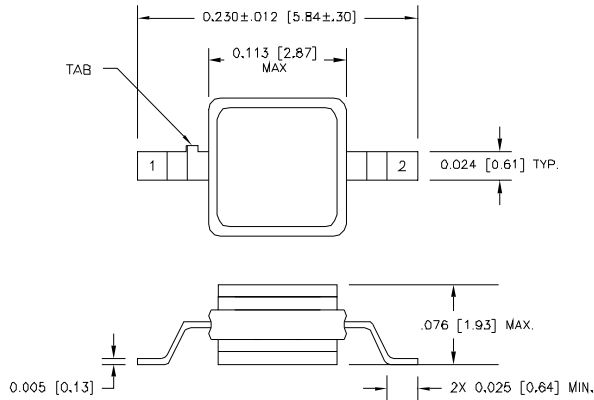
$$I_D V_D < (T_J - T_{L}) / R_{TH}, j-l \text{ and } T_L = T_{LEAD}$$



Typical Performance (50Ω test fixture with bias tees) $V_G = 5.0V$



Package Dimensions



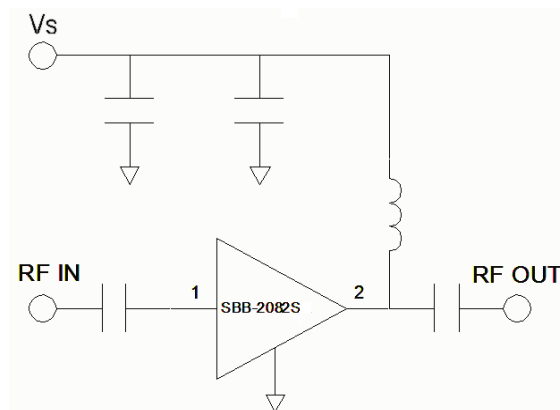
Package Pin Description

| Pin | Function | Description |
|----------------|----------|---|
| 1 | RF IN | This pin is DC coupled and matched to 50Ω. An external DC block is required. |
| 2 | RF OUT | This pin is DC coupled and matched to 50Ω. DC bias is applied through this pin. |
| Package Paddle | GND | Package backside must be connected to RF/DC ground. |

Notes:

1. Dimensions in inches [millimeters].
2. Package material: Ceramic
3. Lead finish: Gold.

Typical Application Schematic



**Package Marking
Ordering Information**

| Part Number | Description |
|-------------|----------------------------|
| SBB-2082S | Two lead hermetic package. |